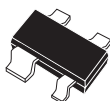


**BAW101****DUAL, ISOLATED HIGH VOLTAGE
SWITCHING DIODES****SOT-143 CASE****CentralTM**
Semiconductor Corp.**DESCRIPTION**

The CENTRAL SEMICONDUCTOR BAW101 type is a Silicon Dual Isolated High Voltage Switching diode designed for surface mount switching applications requiring high voltage capabilities.

Marking Code is CJP.

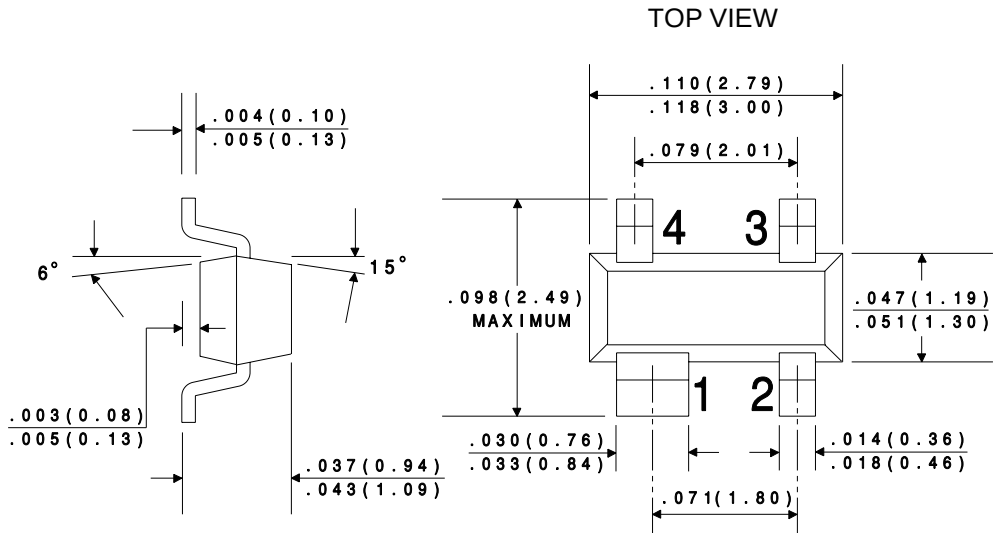
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	300	V
Peak Repetitive Reverse Voltage	V_{RRM}	300	V
Continuous Forward Current	I_F	200	mA
Peak Repetitive Forward Current	I_{FRM}	500	mA
Forward Surge Current, $t_p=1\ \mu\text{s}$	I_{FSM}	4500	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	357	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=250\text{V}$			150	nA
I_R	$V_R=250\text{V}, T_A=150^{\circ}\text{C}$			50	μA
B_{VR}	$I_R=100\mu\text{A}$	300			V
V_F	$I_F=100\text{mA}$		0.9	1.3	V
C_T	$V_R=0\text{V}, f=1.0\text{MHz}$			5.0	pF
t_{rr}	$I_F=I_R=30\text{mA}, I_{rr}=3.0\text{mA}, R_L=100\Omega$			50	ns

All Dimensions in Inches (mm).



LEAD CODE:

- 1) Cathode 1
- 2) Cathode 2
- 3) Anode 2
- 4) Anode 1